

EM-1712

Shipped in packet-tape reel(5000pcs/Reel)

EM-1712 is ultra-small Hall effect ICs of a single silicon chip composed of Hall element and a signal processing IC.

Bipolar Hall Effect Latch Supply Voltage 1.6~5.5 V

Power down Function

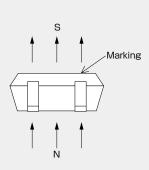
Ultra High Sensitivity Bop:1.8mT

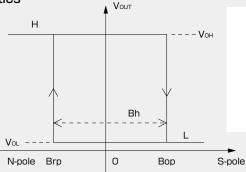
Output **CMOS**

SMT

Notice: It is requested to read and accept "IMPORTANT NOTICE" written on the back of the front cover of this catalogue.

Operational Characteristics







Magnetic flux density

● Absolute Maximum Ratings (Ta=25°C)

| Item | Symbol | Min. | Max. | Unit | |
|---------------------------|-----------------|------|----------------------|------|--|
| Supply Voltage | V _{DD} | -0.1 | 6.0 | V | |
| PDN input voltage | VIN | -0.1 | V _{DD} +0.1 | ٧ | |
| PDN input current | lin | -10 | +10 | mA | |
| Output Current | Іоит | -0.5 | +0.5 | mA | |
| Storage Temperature Range | Тѕтс | -40 | +125 | °C | |

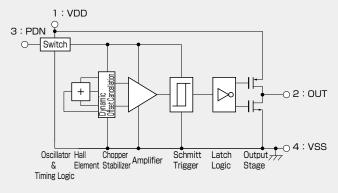
Recommended Operating Conditions

| Item | Symbol | Min. | Тур. | Max. | Unit |
|-----------------------------|-----------------|------|------|------|------|
| Supply Voltage | V _{DD} | 1.6 | 3.0 | 5.5 | ٧ |
| Operating Temperature Range | Topr | -30 | +25 | +85 | °C |

■Magnetic ① and Electrical Characteristics (Ta=25°C VDD=3.0V)

| Item | Symbol | Conditions | Min. | Тур. | Max. | Unit |
|-----------------------------|-------------------|---------------|----------------------|------|--------|------|
| Operating Point *1 | Вор | | | 1.8 | 4.0 | mT |
| Releasing Point *1 | Brp | | -4.0 | -1.8 | | mT |
| Hysteresis | Bh | | | 3.6 | | mT |
| PDN input High voltage | VIH | | 0.7V _{DD} | | | V |
| PDN input Low voltage | VIL | | | | 0.3 | V |
| Output High Voltage | Vон | lo=-0.5mA | V _{DD} -0.4 | | | V |
| Output Low Voltage | Vol | Io=+0.5mA | | | 0.4 | V |
| Supply Current1*2 | loo1 | PDN=L | | | 1 | μΑ |
| Supply Current2*2 | loo2 | PDN=H,Average | | 60 | 150 | μΑ |
| PDN input Current | lin | | -1 | | 1 | μΑ |
| PDN mode transition time1*3 | Tpd1 | Active→PDN | | | (36.6) | μs |
| PDN mode transition time2 | T _{PD} 2 | PDN→Active | | | 100 | μs |
| 1 [mT] =10 [Gauss] | | | | | | |

Functional Block Diagram



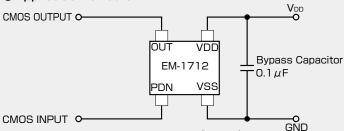
| Item | Symbol | Conditions | Min. | Тур. | Max. | Unit |
|-----------------------|-------------------|------------|------|------|------|------|
| Pulse Drive Period | T _{PD} 3 | PDN=H | 0.5 | 1.0 | 1.5 | ms |
| PDN input Pluse Width | Tw | | 100 | | | μs |
| Pulse Drive Time | T _{PD} 4 | PDN=H | 12.2 | 24.4 | 36.6 | μs |

■Magnetic Characteristics ② (Ta=-30~+85°C VDD=3.0V)

| Parameter | Symbol | Conditions | Min. | Тур. | Max. | Unit |
|-----------------|--------|------------|------|------|------|------|
| Operating Point | Вор | | | 1.8 | 4.2 | mT |
| Releasing Point | Brp | | -4.2 | -1.8 | | mT |
| Hysteresis | Bh | | | 3.6 | | mT |

Note) The above specifications are design targets.

Application Circuit



- *1: Positive("+") polarity flux is defined as the magnetic flux from south polewhich is direct toward to the branded face of the sensor (Bop,Brp)
 *2: In case of PDN pin is held at VDD or GND.
 *3: This transition time is not guarantee

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Package (Unit:mm) ●(For reference only)Land Pattern (Unit:mm) 0.25 0.50 03 2 φ0.3 2.1±0.2 0~0.1 Sensor center 0.90 S 8 3 0.05 0.1 Sensor çenter Note 1) The sensor center is located within the ϕ 0.3mm circle. 0.55 က Note2) The tolerances of dimensions with no mentions is ± 0.1 mm. Note3) Coplanarity: The differences between <u>5°</u> standoff of terminals are max.0.1mm. 1.30 Pin No. Note4) The sensor part is located 0.4mm(typ.) Pin Name | Function far from marking surface. VDD Power Supply OUT Output PDN Power Down

Function Timing Chart 1 B[mT] Bop O Brp VPDN [V] VOUT [V] O Undefined TPD1(<36.6µs) Functional Timing

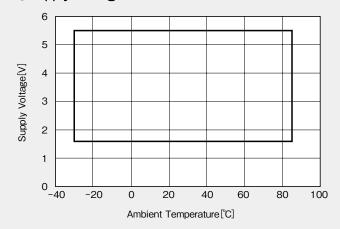
Note1) During power down mode, output is latched in its previous state.

Note2) When VDD is supplied, the time from reaching V_{DD}=
1.6V to the update of the output state is equal to T_{PD}2.

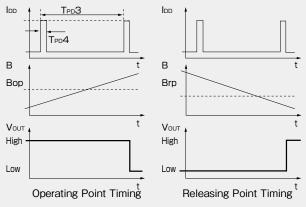
Supply Voltage

VSS

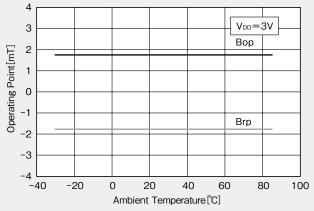
Ground



●Function Timing Chart 2 (PDN=H)



●Temperature Dependence of Bop. Brp



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